

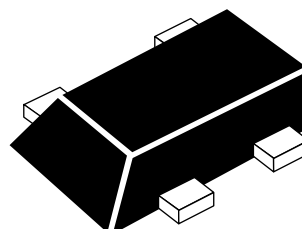


NEC's NPN SiGe HIGH FREQUENCY TRANSISTOR

NESG2101M05

FEATURES

- **HIGH BREAKDOWN VOLTAGE SiGe TECHNOLOGY**
 $V_{CE0} = 5 \text{ V}$ (Absolute Maximum)
- **HIGH OUTPUT POWER:**
 $P_{1dB} = 21 \text{ dBm}$ at 2 GHz
- **LOW NOISE FIGURE:**
 $NF = 0.9 \text{ dB}$ at 2 GHz
- **HIGH MAXIMUM STABLE POWER GAIN:**
 $MSG = 17 \text{ dB}$ at 2 GHz
- **LOW PROFILE M05 PACKAGE:**
SOT-343 footprint, with a height of only 0.59 mm
Flat lead style for better RF performance



M05

DESCRIPTION

NEC's NESG2101M05 is fabricated using NEC's high voltage Silicon Germanium process (UHS2-HV), and is designed for a wide range of applications including low noise amplifiers, medium power amplifiers, and oscillators

NEC's low profile, flat lead style M05 Package provides high frequency performance for compact wireless designs.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PART NUMBER PACKAGE OUTLINE			NESG2101M05 M05			
SYMBOLS		PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
RF	P_{1dB}	Output Power at 1 dB Compression Point $V_{CE} = 3.6 \text{ V}$, $I_{CQ} = 10 \text{ mA}$, $f = 2 \text{ GHz}$	dBm		21	
	G_L	Linear Gain, $V_{CE} = 3.6 \text{ V}$, $I_{CQ} = 10 \text{ mA}$, $f = 2 \text{ GHz}$	dB		15	
	NF	Noise Figure at $V_{CE} = 2 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 2 \text{ GHz}$, $Z_S = Z_{SOPT}$, $Z_L = Z_{LOPT}$	dB		0.9	1.2
	G_a	Associated Gain at $V_{CE} = 2 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 2 \text{ GHz}$, $Z_S = Z_{SOPT}$, $Z_L = Z_{LOPT}$	dB	11.0	13.0	
	NF	Noise Figure at $V_{CE} = 2 \text{ V}$, $I_C = 7 \text{ mA}$, $f = 1 \text{ GHz}$, $Z_S = Z_{SOPT}$, $Z_L = Z_{LOPT}$	dB		0.6	
	G_a	Associated Gain at $V_{CE} = 2 \text{ V}$, $I_C = 7 \text{ mA}$, $f = 1 \text{ GHz}$, $Z_S = Z_{SOPT}$, $Z_L = Z_{LOPT}$	dB		19.0	
	MSG	Maximum Stable Gain ¹ at $V_{CE} = 3 \text{ V}$, $I_C = 50 \text{ mA}$, $f = 2 \text{ GHz}$	dB	14.5	17.0	
	IS_{21EI}^2	Insertion Power Gain at $V_{CE} = 3 \text{ V}$, $I_C = 50 \text{ mA}$, $f = 2 \text{ GHz}$	dB	11.5	13.5	
	f_T	Gain Bandwidth Product at $V_{CE} = 3 \text{ V}$, $I_C = 50 \text{ mA}$, $f = 2 \text{ GHz}$	GHz	14	17	
DC	C_{re}	Reverse Transfer Capacitance ² at $V_{CB} = 2 \text{ V}$, $I_C = 0 \text{ mA}$, $f = 1 \text{ MHz}$	pF		0.4	0.5
	I_{CBO}	Collector Cutoff Current at $V_{CB} = 5 \text{ V}$, $I_E = 0$	nA			100
	I_{EBO}	Emitter Cutoff Current at $V_{EB} = 1 \text{ V}$, $I_C = 0$	nA			100
	h_{FE}	DC Current Gain ³ at $V_{CE} = 2 \text{ V}$, $I_C = 15 \text{ mA}$		130	190	260

Notes:

1. $MSG = \left| \frac{S_{21}}{S_{12}} \right|$

2. Collector to base capacitance is measured by capacitance meter (automatic balance bridge method) when emitter pin is connected to the guard pin.

3. Pulsed measurement, pulse width $\leq 350 \mu\text{s}$, duty cycle $\leq 2\%$.

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{CB0}	Collector to Base Voltage	V	13.0
V _{CEO}	Collector to Emitter Voltage	V	5.0
V _{EB0}	Emitter to Base Voltage	V	1.5
I _C	Collector Current	mA	100
P _T ²	Total Power Dissipation	mW	500
T _J	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to +150

Note:

1. Operation in excess of any one of these parameters may result in permanent damage.
2. Mounted on 38 x 38 x 0.4 mm (t) glass epoxy substrate

THERMAL RESISTANCE

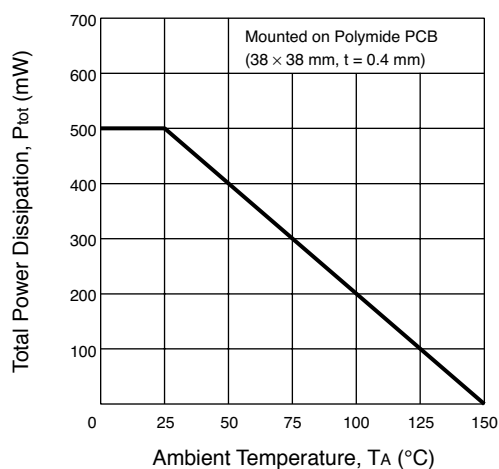
SYMBOLS	PARAMETERS	UNITS	RATINGS
R _{th j-c}	Junction to Case Resistance	°C/W	TBD

ORDERING INFORMATION

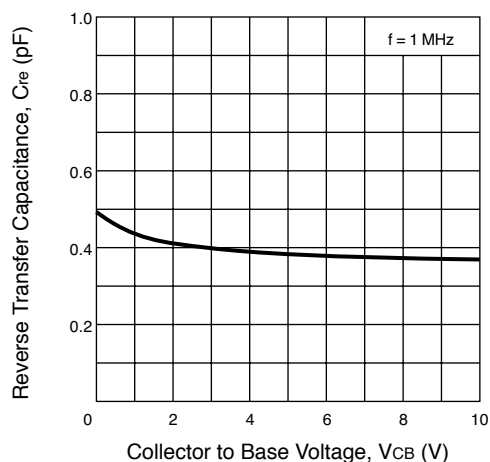
PART NUMBER	QUANTITY	SUPPLYING FORM
NESG2101M05-T1-A	3 kpcs/reel	• Pin 3 (Collector), Pin 4 (Emitter) face the perforation side of the tape • 8 mm wide embossed taping

TYPICAL PERFORMANCE CURVES (T_A = 25°C)

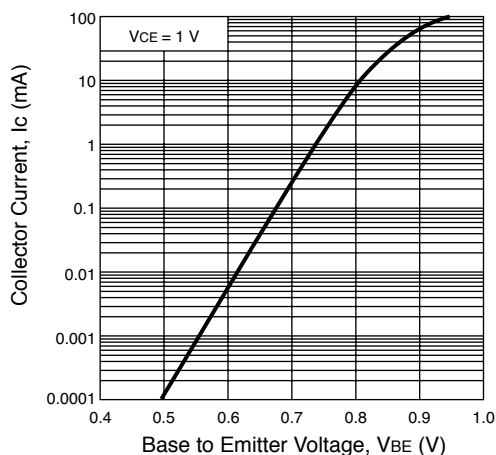
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



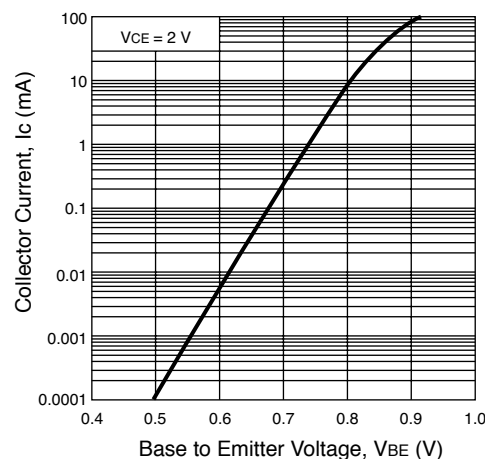
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

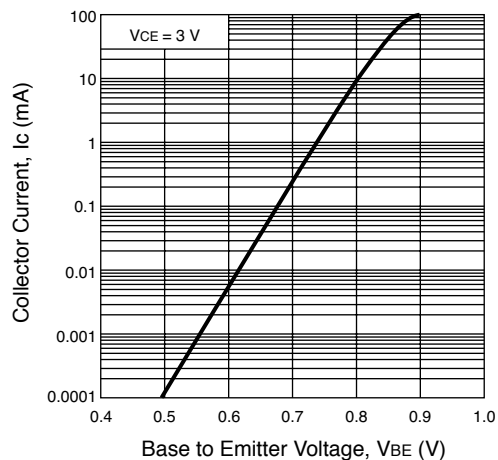


COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

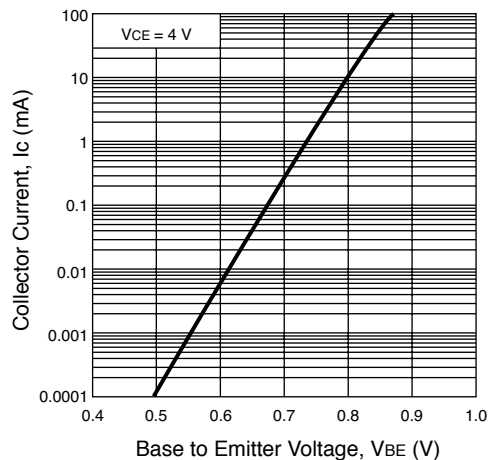


TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)

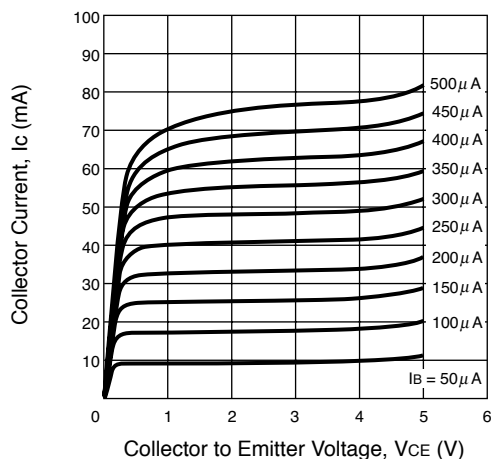
**COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE**



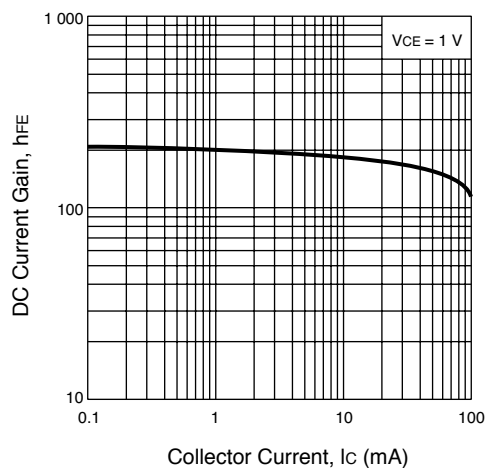
**COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE**



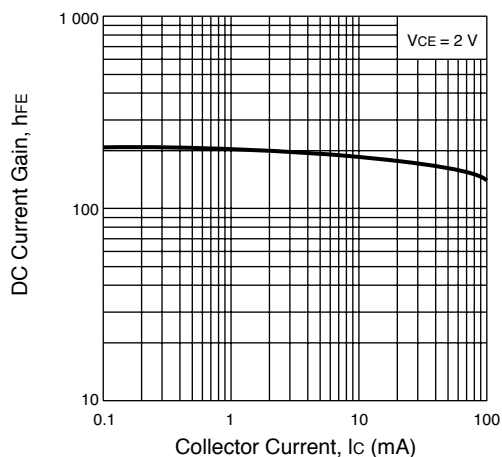
**COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE**



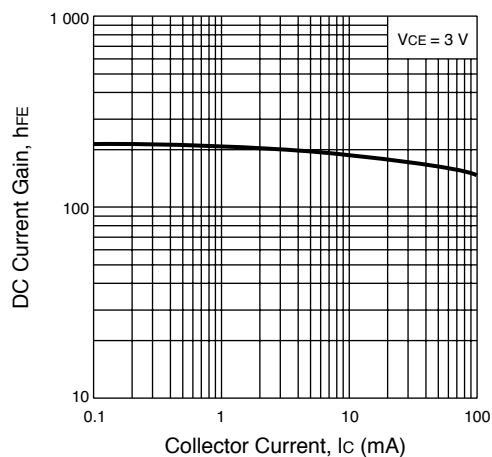
**DC CURRENT GAIN vs.
COLLECTOR CURRENT**



**DC CURRENT GAIN vs.
COLLECTOR CURRENT**

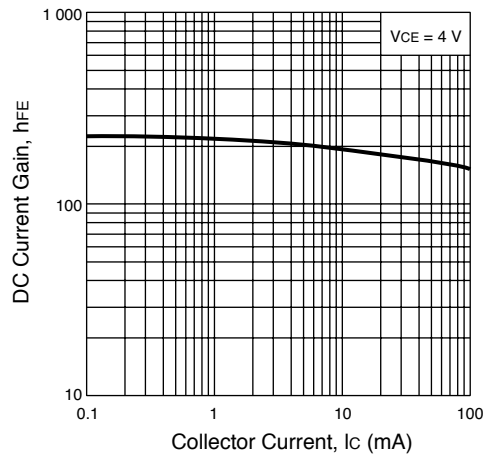


**DC CURRENT GAIN vs.
COLLECTOR CURRENT**

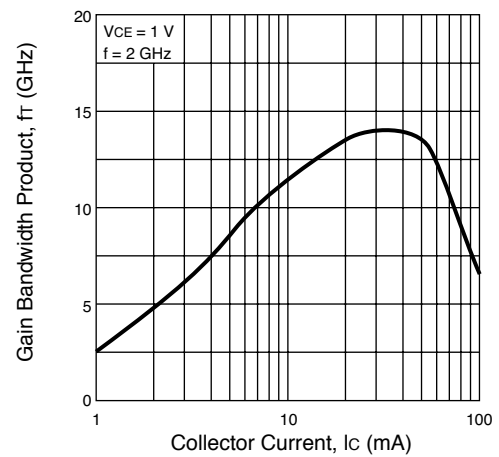


TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)

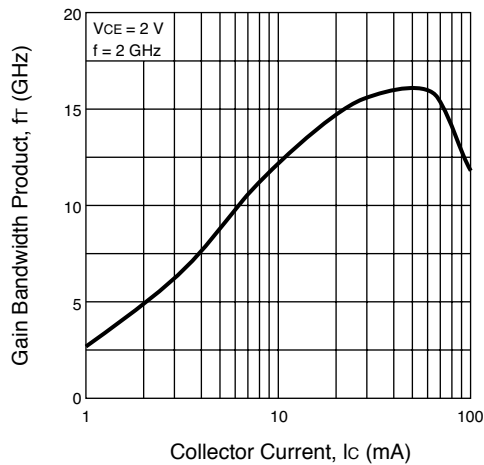
**DC CURRENT GAIN vs.
COLLECTOR CURRENT**



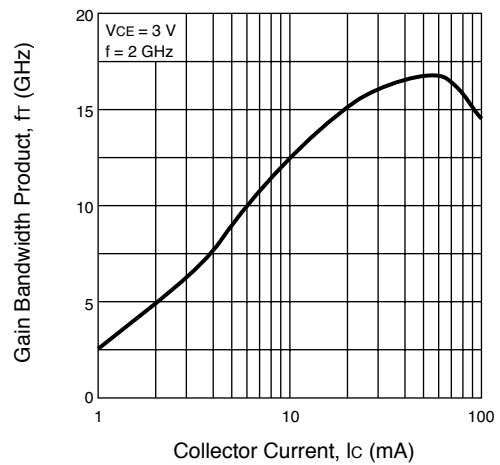
**GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT**



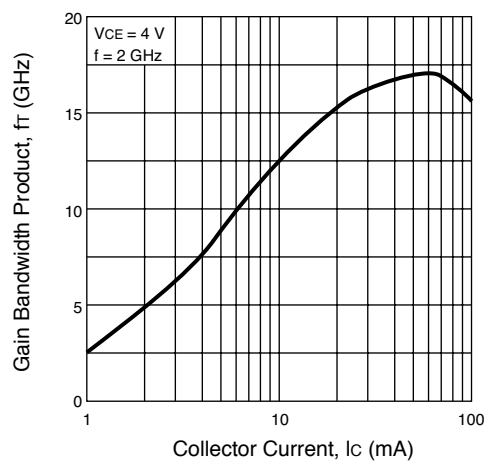
**GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT**



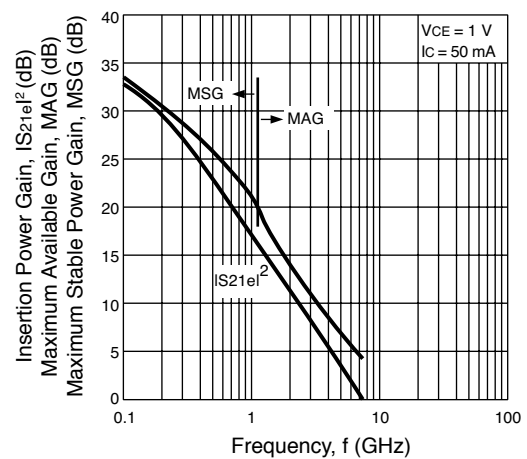
**GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT**



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vs. COLLECTOR CURRENT**

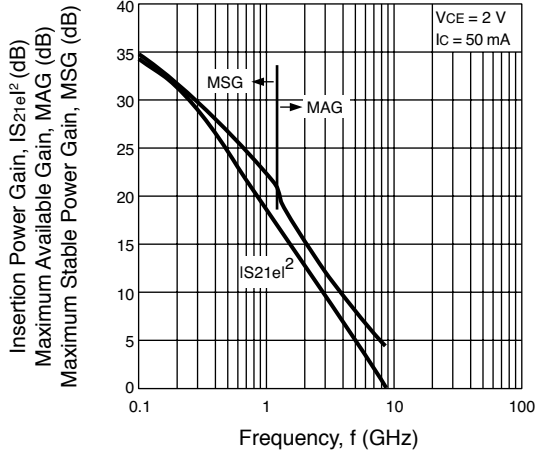


**INSERTION POWER GAIN, MAG, MSG
vs. FREQUENCY**

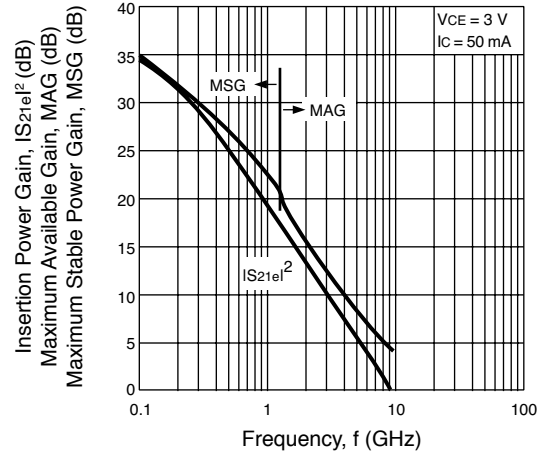


TYPICAL PERFORMANCE CURVES (T_A = 25°C)

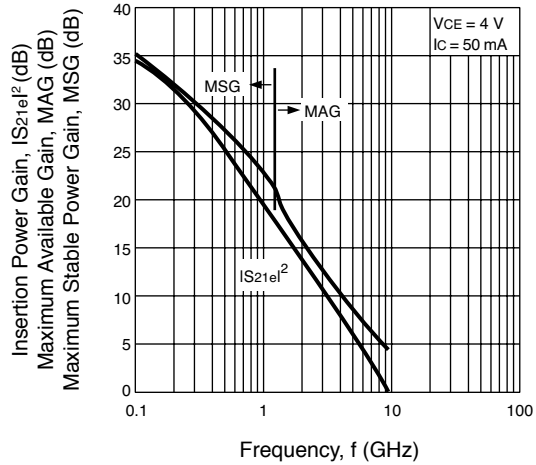
**INSERTION POWER GAIN, MAG, MSG
vs. FREQUENCY**



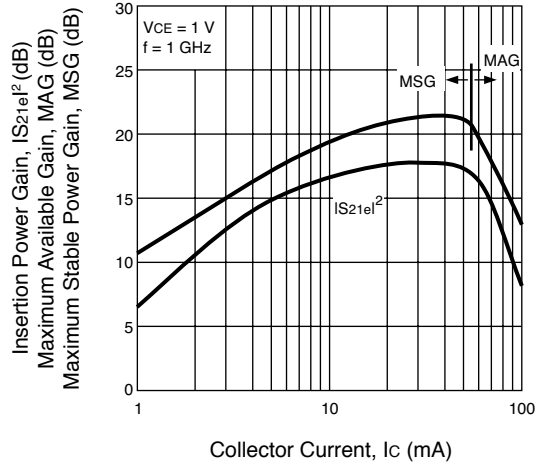
**INSERTION POWER GAIN, MAG, MSG
vs. FREQUENCY**



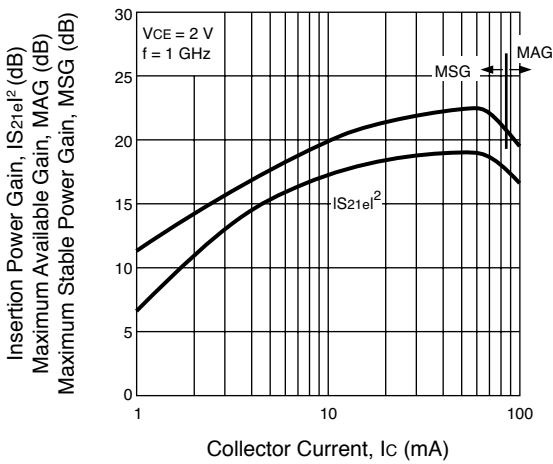
**INSERTION POWER GAIN, MAG, MSG
vs. FREQUENCY**



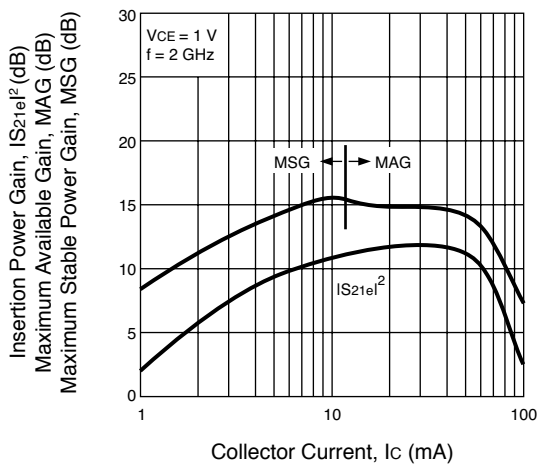
**INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT**

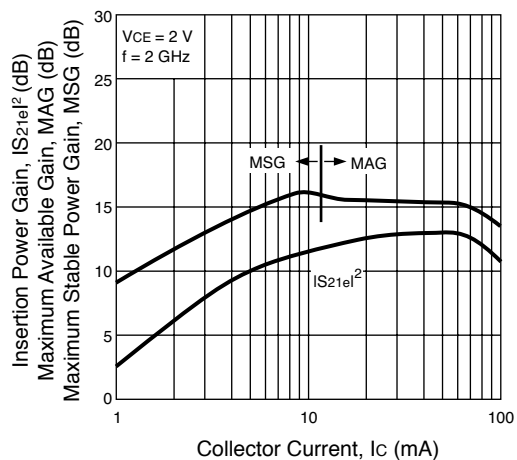
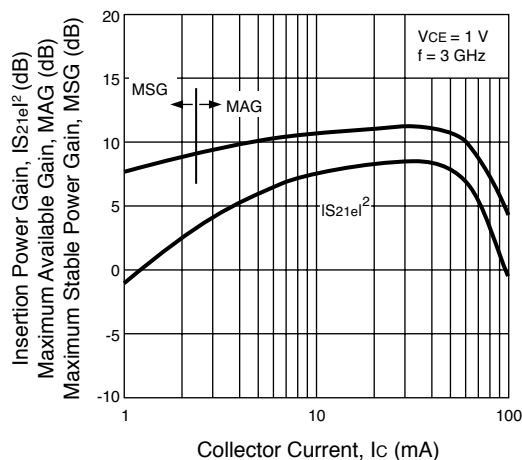
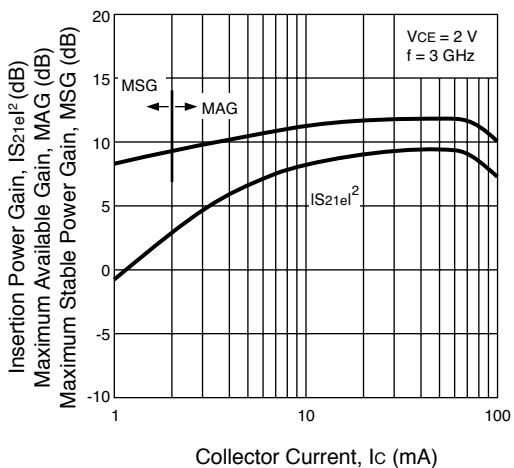
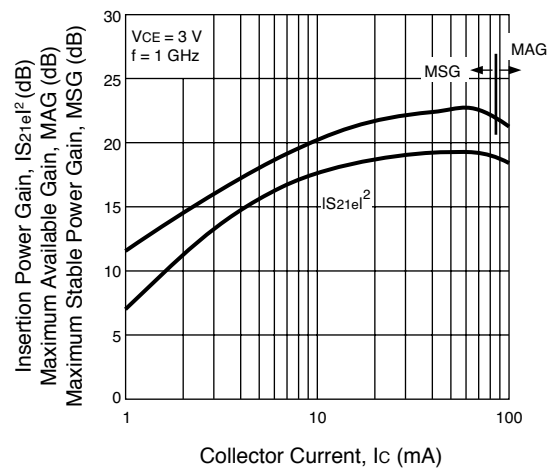
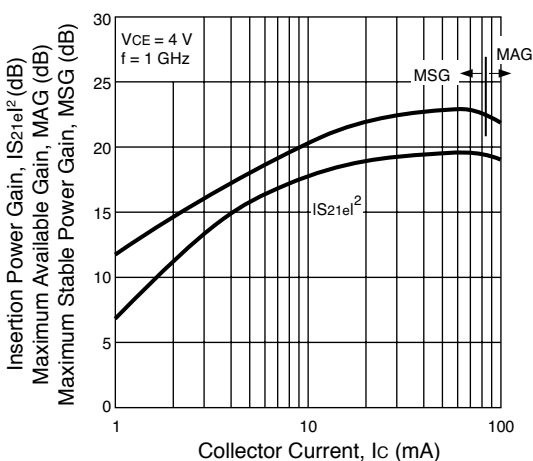
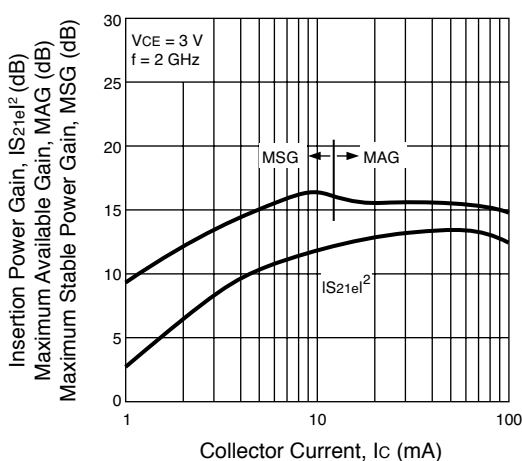


**INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT**



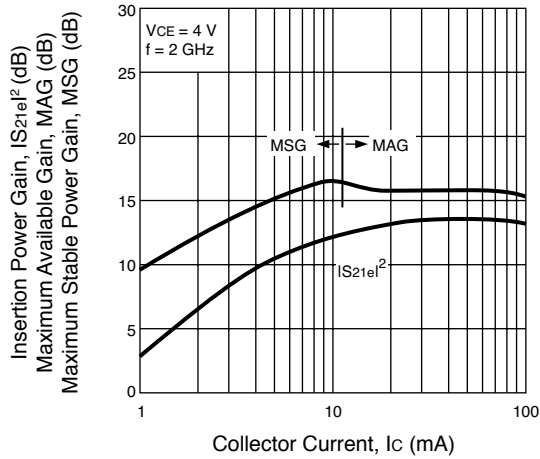
**INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT**



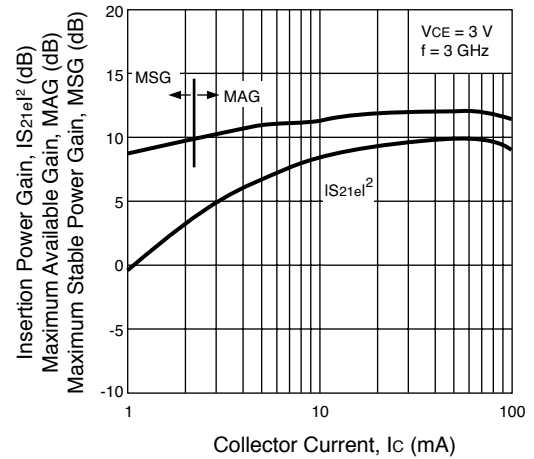
TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)INSERTION POWER GAIN, MAG,
MSG vs. COLLECTOR CURRENTINSERTION POWER GAIN, MAG,
MSG vs. COLLECTOR CURRENTINSERTION POWER GAIN, MAG, MSG
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MSG vs. COLLECTOR CURRENTINSERTION POWER GAIN, MAG,
MSG vs. COLLECTOR CURRENTOUTPUT POWER, COLLECTOR CURRENT
vs. INPUT POWER

TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)

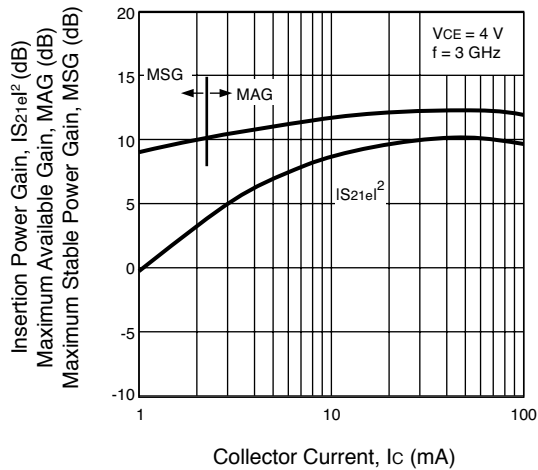
**INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT**



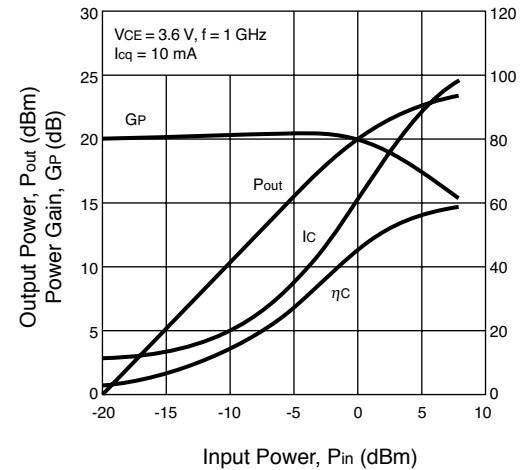
**INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT**



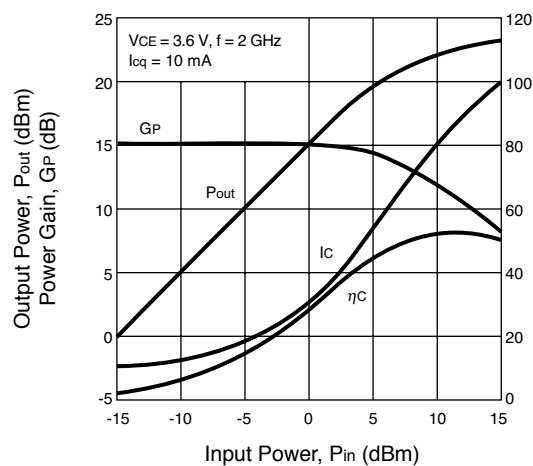
**INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT**



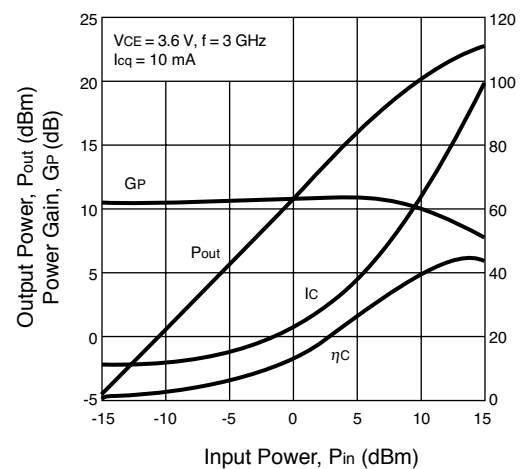
**OUTPUT POWER, POWER GAIN, COLLECTOR
CURRENT, COLLECTOR EFFICIENCY
vs. INPUT POWER**



**OUTPUT POWER, POWER GAIN, COLLECTOR
CURRENT, COLLECTOR EFFICIENCY
vs. INPUT POWER**

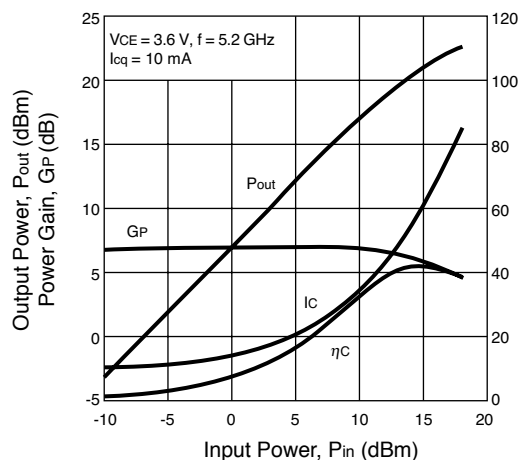


**OUTPUT POWER, POWER GAIN, COLLECTOR
CURRENT, COLLECTOR EFFICIENCY
vs. INPUT POWER**

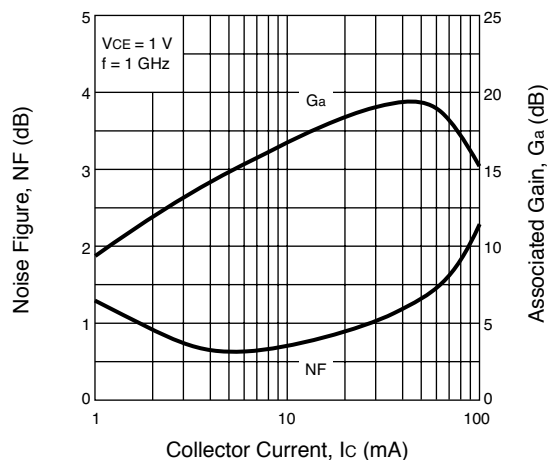


TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)

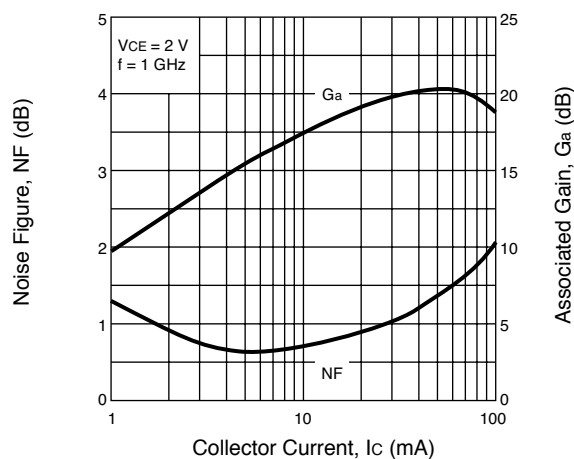
OUTPUT POWER, POWER GAIN, COLLECTOR CURRENT, COLLECTOR EFFICIENCY vs. INPUT POWER



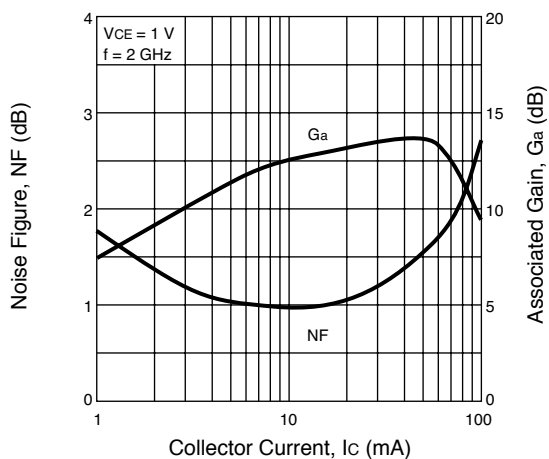
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



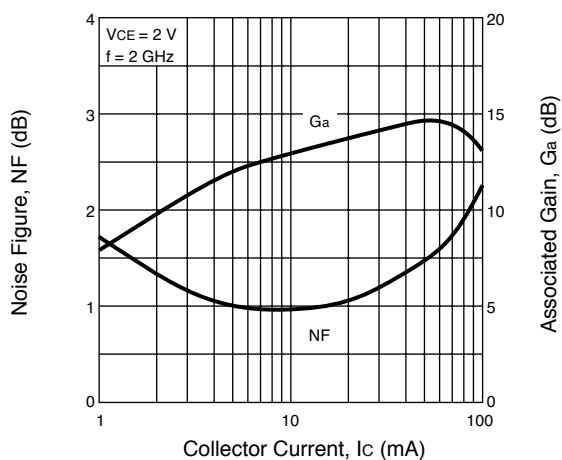
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



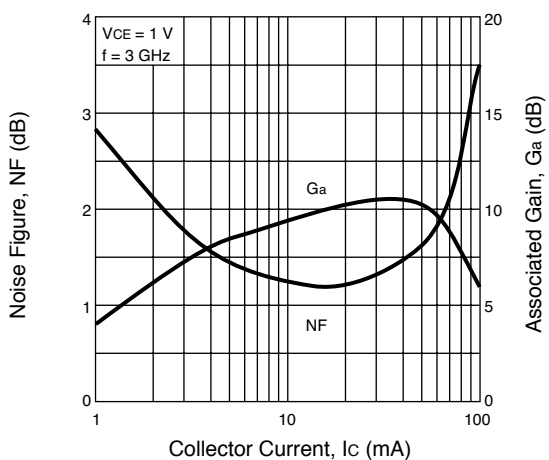
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT

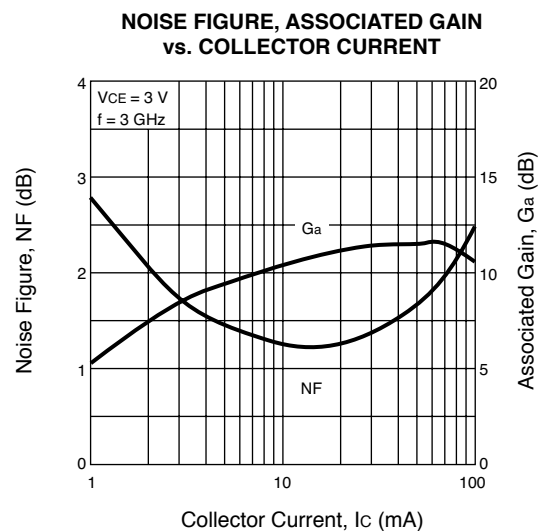
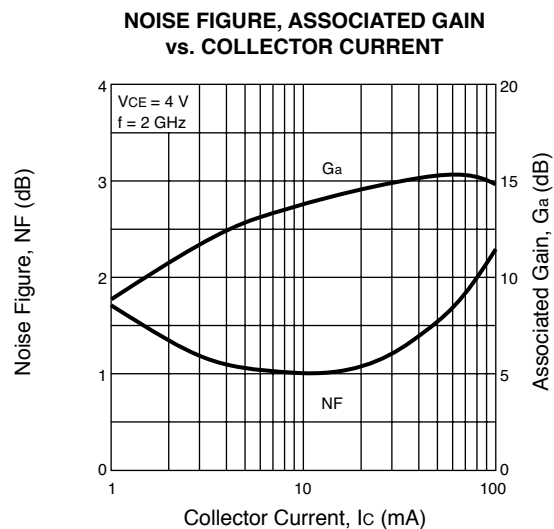
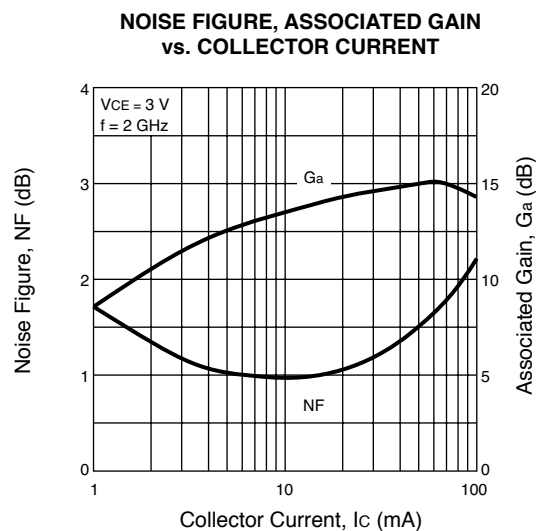
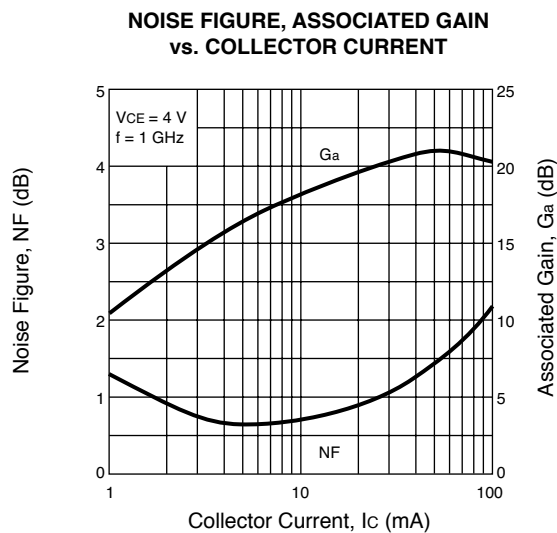
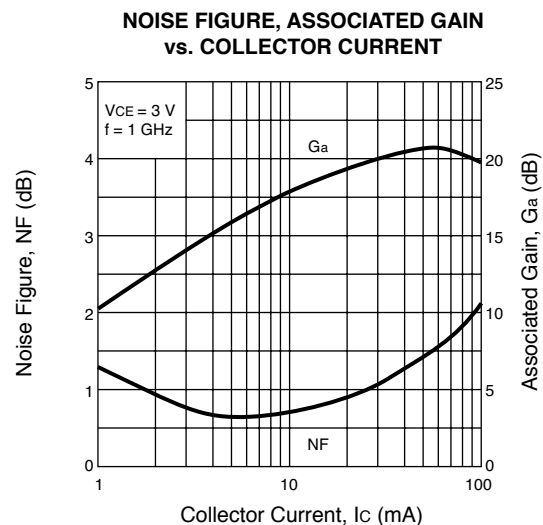
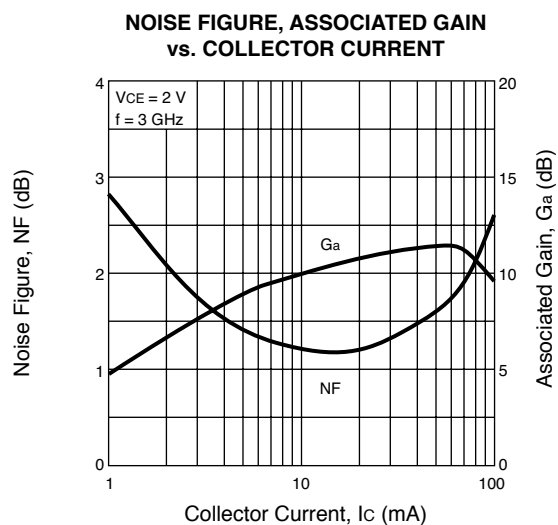


NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT

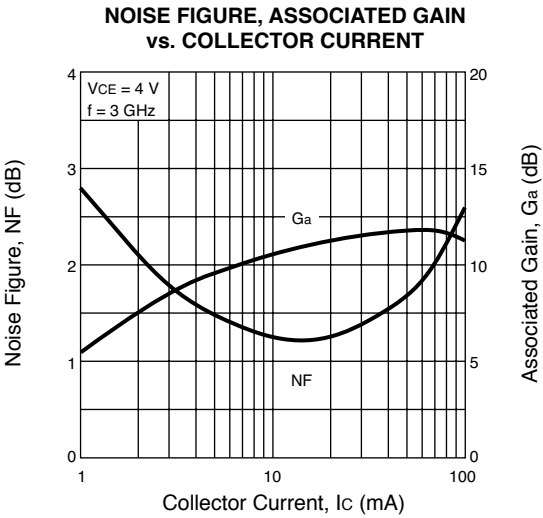


NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



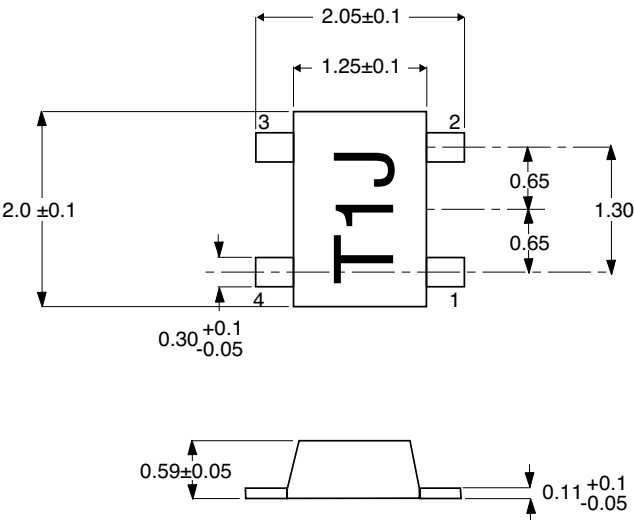
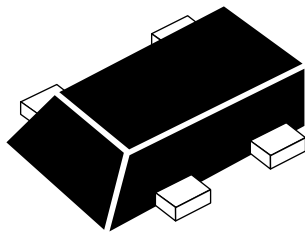
TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)

TYPICAL PERFORMANCE CURVES (TA = 25°C)



OUTLINE DIMENSIONS (Units in mm)

PACKAGE OUTLINE M05
FLAT LEAD 4-PIN THIN TYPE SUPER MINIMOLD

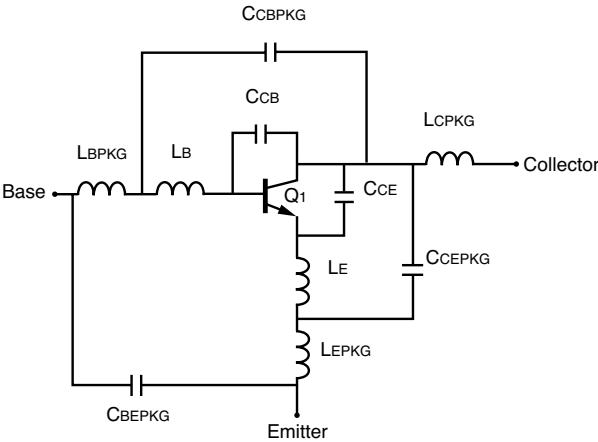


PIN CONNECTIONS

- 1. Base
- 2. Emitter
- 3. Collector
- 4. Emitter

NONLINEAR MODEL

SCHEMATIC



BJT NONLINEAR MODEL PARAMETERS⁽¹⁾

Parameters	Q1	Parameters	Q1
IS	3.64e-15	MJC	0.149
BF	309.7	XCJC	1
NF	1.079	CJS	0
VAF	56	VJS	0.75
IKF	233.9	MJS	0
ISE	11.67e-15	FC	0.8
NE	1.648	TF	4e-12
BR	20.01	XTF	10
NR	1.080	VTF	5
VAR	2.782	ITF	0.5
IKR	54.57e-3	PTF	20
ISC	1.024e-18	TR	0
NC	1.35	EG	1.11
RE	1.6	XTB	1.3
RB	2.2	XTI	5.2
RBM	0.05	KF	0
IRB	1e-4	AF	1
RC	4.8		
CJE	1.461e-12		
VJE	0.798		
MJE	0.137		
CJC	489.9e-15		
VJC	0.605		

(1) Gummel-Poon Model

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

CEL California Eastern Laboratories, Your source for NEC RF, Microwave, Optoelectronic, and Fiber Optic Semiconductor Devices.
4590 Patrick Henry Drive • Santa Clara, CA 95054-1817 • (408) 988-3500 • FAX (408) 988-0279 • www.cel.com

DATA SUBJECT TO CHANGE WITHOUT NOTICE

ADDITIONAL PARAMETERS

Parameters	NESG2101M05
CCB	0.01 pF
CCE	0.2 pF
LB	0.16 nH
LE	0.17 nH
CCBPKG	0.45 pF
CCEPKG	0.02 pF
CBEPKG	0.05 pF
LBPKG	0.8 nH
LCPKG	1.2 nH
LEPKG	0.15 nH

MODEL TEST CONDITIONS

Frequency: 0.1 to 6 GHz
Bias: VCE = 2 V, IC = 5 mA to 40 mA
Date: 09/2003

Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
		-A	-AZ
Lead (Pb)	< 1000 PPM	Not Detected	(*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
PBB	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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